



PATENT
Attorney Docket No. ASC-044C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Fitzgerald *et al.*
SERIAL NO.: 10/611,739 GROUP NO.: 2818
FILING DATE: July 1, 2003 EXAMINER: Dung Anh Le
TITLE: METHOD OF FABRICATING CMOS INVERTER AND
INTEGRATED CIRCUITS UTILIZING STRAINED SILICON
SURFACE CHANNEL MOSFETS

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98(a)(2)(i), only copies of the foreign patent documents and non-patent publications are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☐ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☒ (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and

☐ the requisite Statement is below, **OR**

05/06/2004 AWONDAF1 00000042 10611739

01 FC:1806

180.00 DP

- ☒ the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or
- ☐ (3) after the mailing date of a **final action** or **notice of allowance** but before the payment of the **issue fee**, **AND**
- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.


It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

In addition, Applicants wish to inform the Examiner about the following co-pending patent application, including the Office actions issued therein:

- 1) 10/625,018, filed on July 23, 2003, by Fitzgerald *et al.*

Applicants believe that no additional fees are due for this paper to be entered and considered, but the Commissioner is hereby authorized to charge Deposit Account No. 20-0531 for any required fees that may be due.

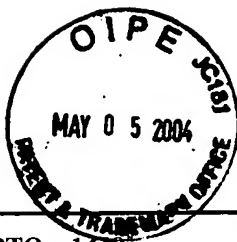
Respectfully submitted,



Natasha C. Us
Attorney for Applicant(s)
Testa, Hurwitz & Thibault, LLP
High Street Tower
125 High Street
Boston, Massachusetts 02110

Date: April 30, 2004
Reg. No. 44,381

Tel. No.: (617) 310-8327
Fax No.: (617) 248-7100



| FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT | | | | ATTORNEY DOCKET NO.: ASC-044C1 APPLICANT(S): Fitzgerald <i>et al.</i> SERIAL NO.: 10/611,739 FILING DATE: July 1, 2003 GROUP: 2818 | | | |
|---|-----|--------------------|------------|---|-------|--------------|-------------------------------|
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | A1 | 2001/0003364 | 06/14/2001 | Sugawara <i>et al.</i> | | | |
| | A2 | 2002/0100942 | 08/01/2002 | Fitzgerald <i>et al.</i> | | | |
| | A3 | 2002/0043660 | 04/18/2002 | Yamazaki <i>et al.</i> | | | |
| | A4 | 2002/0096717 | 07/25/2002 | Chu <i>et al.</i> | | | |
| | A5 | 2002/0123167 | 09/05/2002 | Fitzgerald | | | |
| | A6 | 2002/0123183 | 09/05/2002 | Fitzgerald | | | |
| | A7 | 2002/0123197 | 09/05/2002 | Fitzgerald <i>et al.</i> | | | |
| | A8 | 2002/0125471 | 09/12/2002 | Fitzgerald <i>et al.</i> | | | |
| | A9 | 2002/0125497 | 09/12/2002 | Fitzgerald | | | |
| | A10 | 2002/0140031 | 10/03/2002 | Rim | | | |
| | A11 | 2002/0168864 | 11/14/2002 | Cheng <i>et al.</i> | | | |
| | A12 | 2003/0003679 | 01/02/2003 | Doyle <i>et al.</i> | | | |
| | A13 | 2003/0013323 | 01/16/2003 | Hammond <i>et al.</i> | | | |
| | A14 | 2003/0025131 | 02/06/2003 | Lee <i>et al.</i> | | | |
| | A15 | 2003/0057439 | 03/27/2003 | Fitzgerald | | | |
| | A16 | 4,010,045 | 03/01/1977 | Ruehrwein | | | |
| | A17 | 4,710,788 | 12/01/1987 | Dämbkes <i>et al.</i> | | | |
| | A18 | 4,990,979 | 02/05/1991 | Otto | | | |
| | A19 | 4,994,866 | 02/01/1991 | Awano | | | |
| | A20 | 4,997,776 | 03/05/1991 | Haramé <i>et al.</i> | | | |
| | A21 | 5,013,681 | 05/07/1991 | Godbey <i>et al.</i> | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |

| FORM PTO - 1449 | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | |
|----------------------------------|-----|--------------------|------------|--|-------|--------------|-------------------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | |
| | | | | SERIAL NO.: 10/611,739 | | | |
| | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | A22 | 5,155,571 | 10/13/1992 | Wang <i>et al.</i> | | | |
| | A23 | 5,166,084 | 11/24/1992 | Pfiester | | | |
| | A24 | 5,177,583 | 01/05/1993 | Endo <i>et al.</i> | | | |
| | A25 | 5,202,284 | 04/13/1993 | Kamins <i>et al.</i> | | | |
| | A26 | 5,207,864 | 05/04/1993 | Bhat <i>et al.</i> | | | |
| | A27 | 5,208,182 | 05/04/1993 | Narayan <i>et al.</i> | | | |
| | A28 | 5,212,110 | 05/18/1993 | Pfiester <i>et al.</i> | | | |
| | A29 | 5,221,413 | 06/22/1993 | Brasen <i>et al.</i> | | | |
| | A30 | 5,241,197 | 08/31/1993 | Murakami <i>et al.</i> | | | |
| | A31 | 5,250,445 | 10/05/1993 | Bean <i>et al.</i> | | | |
| | A32 | 5,285,086 | 02/08/1994 | Fitzgerald | | | |
| | A33 | 5,291,439 | 03/01/1994 | Kauffmann <i>et al.</i> | | | |
| | A34 | 5,298,452 | 03/29/1994 | Meyerson | | | |
| | A35 | 5,310,451 | 05/10/1994 | Tejwani <i>et al.</i> | | | |
| | A36 | 5,316,958 | 05/31/1994 | Meyerson | | | |
| | A37 | 5,346,848 | 09/13/1994 | Gruppen-Shemansky <i>et al.</i> | | | |
| | A38 | 5,374,564 | 12/20/1994 | Bruel | | | |
| | A39 | 5,399,522 | 03/21/1995 | Ohuri | | | |
| | A40 | 5,413,679 | 05/09/1995 | Godbey | | | |
| | A41 | 5,426,069 | 06/20/1995 | Selvakumar <i>et al.</i> | | | |
| | A42 | 5,426,316 | 06/20/1995 | Mohammad | | | |
| | A43 | 5,442,205 | 08/15/1995 | Brasen <i>et al.</i> | | | |
| | A44 | 5,461,243 | 10/24/1995 | Ek <i>et al.</i> | | | |
| | A45 | 5,461,250 | 10/24/1995 | Burghartz <i>et al.</i> | | | |
| | A46 | 5,462,883 | 10/31/1995 | Dennard <i>et al.</i> | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |

| FORM PTO – 1449 | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | |
|---|-----|----------------------------|-------------|---|--------------|----------------------|---------------------------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | |
| | | | | SERIAL NO.: 10/611,739 | | | |
| | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | A47 | 5,476,813 | 12/19/1995 | Naruse | | | |
| | A48 | 5,479,033 | 12/26/1995 | Baca <i>et al.</i> | | | |
| | A49 | 5,484,664 | 01/16/1996 | Kitahara <i>et al.</i> | | | |
| | A50 | 5,523,243 | 06/04/1996 | Mohammad | | | |
| | A51 | 5,523,592 | 06/04/1996 | Nakagawa <i>et al.</i> | | | |
| | A52 | 5,534,713 | 07/09/1996 | Ismail <i>et al.</i> | | | |
| | A53 | 5,536,361 | 07/16/1996 | Kondo <i>et al.</i> | | | |
| | A54 | 5,540,785 | 07/30/1996 | Dennard <i>et al.</i> | | | |
| | A55 | 5,596,527 | 01/21/1997 | Tomioka <i>et al.</i> | | | |
| | A56 | 5,617,351 | 04/01/1997 | Bertin <i>et al.</i> | | | |
| | A57 | 5,630,905 | 05/20/1997 | Lynch <i>et al.</i> | | | |
| | A58 | 5,659,187 | 08/19/1997 | Legoues <i>et al.</i> | | | |
| | A59 | 5,683,934 | 11/04/1997 | Candelaria | | | |
| | A60 | 5,698,869 | 12/16/1997 | Yoshimi <i>et al.</i> | | | |
| | A61 | 5,714,777 | 02/03/1998 | Ismail <i>et al.</i> | | | |
| | A62 | 5,728,623 | 03/17/1998 | Mori | | | |
| | A63 | 5,739,567 | 04/14/1998 | Wong | | | |
| | A64 | 5,759,898 | 06/02/1998 | Ek <i>et al.</i> | | | |
| | A65 | 5,777,347 | 07/07/1998 | Bartelink | | | |
| | A66 | 5,786,612 | 07/28/1998 | Otani <i>et al.</i> | | | |
| | A67 | 5,792,679 | 08/11/1998 | Nakato | | | |
| | A68 | 5,808,344 | 09/15/1998 | Ismail <i>et al.</i> | | | |
| | A69 | 5,847,419 | 12/08/1998 | Imai <i>et al.</i> | | | |
| | A70 | 5,877,070 | 03/02/1999 | Goesele <i>et al.</i> | | | |
| | A71 | 5,891,769 | 04/06/1999 | Liaw <i>et al.</i> | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |

| FORM PTO – 1449 | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | |
|---|-----|----------------------------|-------------|---|--------------|----------------------|---------------------------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | |
| | | | | SERIAL NO.: 10/611,739 | | | |
| | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | A72 | 5,906,708 | 05/25/1999 | Robinson <i>et al.</i> | | | |
| | A73 | 5,906,951 | 05/25/1999 | Chu <i>et al.</i> | | | |
| | A74 | 5,912,479 | 06/15/1999 | Mori <i>et al.</i> | | | |
| | A75 | 5,943,560 | 08/24/1999 | Chang <i>et al.</i> | | | |
| | A76 | 5,963,817 | 10/05/1999 | Chu <i>et al.</i> | | | |
| | A77 | 5,966,622 | 10/12/1999 | Levine <i>et al.</i> | | | |
| | A78 | 5,998,807 | 12/07/1999 | Lustig <i>et al.</i> | | | |
| | A79 | 6,013,134 | 01/11/2000 | Chu <i>et al.</i> | | | |
| | A80 | 6,033,974 | 03/07/2000 | Henley <i>et al.</i> | | | |
| | A81 | 6,033,995 | 03/07/2000 | Muller | | | |
| | A82 | 6,058,044 | 05/02/2000 | Sugiura <i>et al.</i> | | | |
| | A83 | 6,059,895 | 05/09/2000 | Chu <i>et al.</i> | | | |
| | A84 | 6,074,919 | 06/13/2000 | Gardner <i>et al.</i> | | | |
| | A85 | 6,096,590 | 08/01/2000 | Chan <i>et al.</i> | | | |
| | A86 | 6,103,559 | 08/15/2000 | Gardner <i>et al.</i> | | | |
| | A87 | 6,107,653 | 08/22/2000 | Fitzgerald | | | |
| | A88 | 6,111,267 | 08/29/2000 | Fischer <i>et al.</i> | | | |
| | A89 | 6,117,750 | 09/12/2000 | Bensahel <i>et al.</i> | | | |
| | A90 | 6,130,453 | 10/10/2000 | Mei <i>et al.</i> | | | |
| | A91 | 6,133,799 | 10/17/2000 | Favors <i>et al.</i> | | | |
| | A92 | 6,140,687 | 10/31/2000 | Shimomura <i>et al.</i> | | | |
| | A93 | 6,143,636 | 11/07/2000 | Forbes <i>et al.</i> | | | |
| | A94 | 6,153,495 | 11/28/2000 | Kub <i>et al.</i> | | | |
| | A95 | 6,154,475 | 11/28/2000 | Soref <i>et al.</i> | | | |
| | A96 | 6,160,303 | 12/12/2000 | Fattaruso | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |

| FORM PTO – 1449 | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | |
|---|------|--------------------|------------|---|-------|--------------|-------------------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | |
| | | | | SERIAL NO.: 10/611,739 | | | |
| | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | A97 | 6,162,688 | 12/19/2000 | Gardner <i>et al.</i> | | | |
| | A98 | 6,184,111 | 02/06/2001 | Henley <i>et al.</i> | | | |
| | A99 | 6,191,007 | 02/20/2001 | Matsui <i>et al.</i> | | | |
| | A100 | 6,191,432 | 02/20/2001 | Sugiyama <i>et al.</i> | | | |
| | A101 | 6,194,722 | 02/27/2001 | Fiorini <i>et al.</i> | | | |
| | A102 | 6,204,529 | 03/20/2001 | Lung <i>et al.</i> | | | |
| | A103 | 6,207,977 | 03/27/2001 | Augusto | | | |
| | A104 | 6,210,988 | 04/03/2001 | Howe <i>et al.</i> | | | |
| | A105 | 6,218,677 | 04/17/2001 | Broekaert | | | |
| | A106 | 6,232,138 | 05/15/2001 | Fitzgerald <i>et al.</i> | | | |
| | A107 | 6,235,567 | 05/22/2001 | Huang | | | |
| | A108 | 6,242,324 | 06/05/2001 | Kub <i>et al.</i> | | | |
| | A109 | 6,249,022 | 06/19/2001 | Lin <i>et al.</i> | | | |
| | A110 | 6,251,755 | 06/26/2001 | Furukawa <i>et al.</i> | | | |
| | A111 | 6,261,929 | 07/17/2001 | Gehrke <i>et al.</i> | | | |
| | A112 | 6,266,278 | 07/24/2001 | Harari <i>et al.</i> | | | |
| | A113 | 6,271,551 | 08/07/2001 | Schmitz <i>et al.</i> | | | |
| | A114 | 6,271,726 | 08/07/2001 | Fransis <i>et al.</i> | | | |
| | A115 | 6,291,321 | 09/18/2001 | Fitzgerald | | | |
| | A116 | 6,313,016 | 11/06/2001 | Kibbel <i>et al.</i> | | | |
| | A117 | 6,316,301 | 11/13/2001 | Kant | | | |
| | A118 | 6,323,108 | 11/27/2001 | Kub <i>et al.</i> | | | |
| | A119 | 6,329,063 | 12/11/2001 | Lo <i>et al.</i> | | | |
| | A120 | 6,335,546 | 01/01/2002 | Tsuda <i>et al.</i> | | | |
| | A121 | 6,339,232 | 01/15/2002 | Takagi | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |

| FORM PTO – 1449 | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | | | |
|---|------|-----------------|------------|--|------------------------|-----------|----------------------------|---------------|--------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | | | |
| | | | | SERIAL NO.: 10/611,739 | | | | | |
| | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | | | |
| U.S. PATENT DOCUMENTS | | | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE | | |
| | A122 | 6,350,993 | 02/26/2002 | Chu <i>et al.</i> | | | | | |
| | A123 | 6,368,733 | 04/09/2002 | Nishinaga | | | | | |
| | A124 | 6,372,356 | 04/16/2002 | Thornton <i>et al.</i> | | | | | |
| | A125 | 6,399,970 | 06/04/2002 | Kubo <i>et al.</i> | | | | | |
| | A126 | 6,403,975 | 06/11/2002 | Brunner <i>et al.</i> | | | | | |
| | A127 | 6,407,406 | 06/18/2002 | Tezuka | | | | | |
| | A128 | 6,420,937 | 07/16/2002 | Akatsuka <i>et al.</i> | | | | | |
| | A129 | 6,425,951 | 07/30/2002 | Chu <i>et al.</i> | | | | | |
| | A130 | 6,429,061 | 08/06/2002 | Rim | | | | | |
| | A131 | 6,521,041 | 02/18/2003 | Wu <i>et al.</i> | | | | | |
| | A132 | 6,524,935 | 02/25/2003 | Canaperi <i>et al.</i> | | | | | |
| | A133 | 6,555,839 | 04/29/2003 | Fitzgerald | | | | | |
| | A134 | 6,573,126 | 06/03/2003 | Cheng <i>et al.</i> | | | | | |
| | A135 | 6,583,015 | 06/24/2003 | Fitzgerald <i>et al.</i> | | | | | |
| | A136 | 6,593,191 | 07/15/2003 | Fitzgerald | | | 05/16/2001 | | |
| | A137 | 6,602,613 | 08/05/2003 | Fitzgerald | | | 01/17/2001 | | |
| | A138 | 6,649,480 | 11/18/2003 | Fitzgerald <i>et al.</i> | | | 06/19/2001 | | |
| | A139 | 6,682,965 | 01/27/2004 | Noguchi <i>et al.</i> | | | 03/26/1998 | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
| | B1 | 41 01 167 | 07/23/1992 | DE | | | | N | Abstract only |
| | B2 | 0 514 018 | 11/19/1992 | EP | | | | N | Y |
| | B3 | 0 587 520 | 03/16/1994 | EP | | | | N | Y |
| | B4 | 0 683 522 | 11/22/1995 | EP | | | | N | Y |
| EXAMINER | | | | | DATE CONSIDERED | | | | |

| FORM PTO – 1449 | | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | | |
|---|-----|----------------------------|-------------|-------------------------|---|----------------------|------------------------|--------------------------|-----------------------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | | |
| | | | | | SERIAL NO.: 10/611,739 | | | | |
| | | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
| | B5 | 0 828 296 | 03/11/1998 | EP | | | | N | Y |
| | B6 | 0 829 908 | 03/18/1998 | EP | | | | N | Y |
| | B7 | 0 838 858 | 04/29/1998 | EP | | | | N | N |
| | B8 | 1 020 900 | 07/19/2000 | EP | | | | N | Y |
| | B9 | 1 174 928 | 01/23/2002 | EP | | | | N | Y |
| | B10 | 2 701 599 | 03/21/1995 | FR | | | | N | Abstract only |
| | B11 | 2 342 777 | 04/19/2000 | GB | | | | Y | Y |
| | B12 | 4-307974 | 10/30/1992 | JP | | | | N | Abstract only |
| | B13 | 5-166724 | 07/02/1993 | JP | | | | N | Abstract only |
| | B14 | 6-177046 | 06/24/1994 | JP | | | | N | Abstract only |
| | B15 | 6-244112 | 09/02/1994 | JP | | | | Y | Y |
| | B16 | 6-252046 | 09/09/1994 | JP | | | | Y | Y |
| | B17 | 7-94420 | 04/07/1995 | JP | | | | N | Abstract only |
| | B18 | 7-106446 | 04/21/1995 | JP | | | | N | Abstract only |
| | B19 | 7-240372 | 09/12/1995 | JP | | | | N | Abstract only |
| | B20 | 10-270685 | 10/09/1998 | JP | | | | N | Y |
| | B21 | 11-233744 | 08/27/1999 | JP | | | | N | Abstract only |
| | B22 | 2000-021783 | 01/21/2000 | JP | | | | N | Y |
| | B23 | 2000-031491 | 01/28/2000 | JP | | | | N | Y |
| | B24 | 2001-319935 | 11/16/2001 | JP | | | | N | Y |
| | B25 | 2002-076334 | 03/15/2002 | JP | | | | N | Y |
| | B26 | 2002-164520 | 06/07/2002 | JP | | | | N | Y |
| EXAMINER | | | | | DATE CONSIDERED | | | | |

| FORM PTO – 1449 | | | | | ATTORNEY DOCKET NO.: ASC-044C1 | | | | |
|-----------------------------------|--|--|------------|--------------|--|-----------|-------------|---------------|--------------------|
| INFORMATION DISCLOSURE STATEMENT | | | | | APPLICANT(S): Fitzgerald <i>et al.</i> | | | | |
| | | | | | SERIAL NO.: 10/611,739 | | | | |
| | | | | | FILING DATE: July 1, 2003 GROUP: 2818 | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
| | B27 | 2002-289533 | 10/04/2002 | JP | | | | N | Y |
| | B28 | 98/59365 | 12/30/1998 | WO | | | | N | Y |
| | B29 | 99/53539 | 10/21/1999 | WO | | | | N | Y |
| | B30 | 00/48239 | 08/17/2000 | WO | | | | N | Y |
| | B31 | 00/54338 | 09/14/2000 | WO | | | | N | Y |
| | B32 | 01/022482 | 03/29/2001 | WO | | | | N | Y |
| | B33 | 01/54202 | 07/26/2001 | WO | | | | N | Y |
| | B34 | 01/93338 | 12/06/2001 | WO | | | | N | Y |
| | B35 | 01/99169 | 12/27/2001 | WO | | | | N | Y |
| | B36 | 02/13262 | 02/14/2002 | WO | | | | N | Y |
| | B37 | 02/15244 | 02/21/2002 | WO | | | | N | Y |
| | B38 | 02/27783 | 04/04/2002 | WO | | | | N | Y |
| | B39 | 02/47168 | 06/13/2002 | WO | | | | N | Y |
| | B40 | 02/071488 | 09/12/2002 | WO | | | | N | Y |
| | B41 | 02/071491 | 09/12/2002 | WO | | | | N | Y |
| | B42 | 02/071495 | 09/12/2002 | WO | | | | N | Y |
| | B43 | 02/082514 | 10/17/2002 | WO | | | | N | Y |
| OTHER ART, JOURNAL ARTICLES, ETC. | | | | | | | | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | | | | | | | | |
| | C1 | Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest (1995 International Electron Devices Meeting)</u> , pp. 761-764. | | | | | | | |
| | C2 | Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154. | | | | | | | |
| | C3 | Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258. | | | | | | | |
| | C4 | Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> , Vol. 15 (2001), abstract. | | | | | | | |
| | C5 | Borenstein <i>et al.</i> , "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999), pp. 205-210. | | | | | | | |
| EXAMINER | | | | | DATE CONSIDERED | | | | |

| | | | |
|-----------------------------------|--|--|--|
| FORM PTO – 1449 | | ATTORNEY DOCKET NO.: ASC-044C1 | |
| INFORMATION DISCLOSURE STATEMENT | | APPLICANT(S): Fitzgerald <i>et al.</i> | |
| | | SERIAL NO.: 10/611,739 | |
| | | FILING DATE: July 1, 2003 GROUP: 2818 | |
| OTHER ART, JOURNAL ARTICLES, ETC. | | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | | |
| | C6 | Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS experimental study," <u>IEEE</u> (1996), pp. 21.2.1-21.2.4. | |
| | C7 | Brueel <i>et al.</i> , "@SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179. | |
| | C8 | Brueel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202. | |
| | C9 | Bufler <i>et al.</i> , "Hole transport in strained Si1-xGex alloys on Si1-yGe _y substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602. | |
| | C10 | Burghartz <i>et al.</i> , "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996), pp. 100-104. | |
| | C11 | Canaperi <i>et al.</i> , "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002), abstract. | |
| | C12 | Carlin <i>et al.</i> , "High Efficiency GaAs-on-Si Solar Cells with High Voc using Graded Gesi Buffers," <u>IEEE – 2000</u> (2000), pp. 1006-1011. | |
| | C13 | Chang <i>et al.</i> , "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 202-204. | |
| | C14 | Cheng <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323. | |
| | C15 | Cheng <i>et al.</i> , "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001), pp. L37-L39. | |
| | C16 | Cullis <i>et al.</i> , "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994), pp. 1924-1931. | |
| | C17 | Currie <i>et al.</i> , "Carrier mobilities and process stability of strained Si n- and p-MOSFETs on SiGe virtual substrates," <u>Journal of Vacuum Science and Technology B</u> , Vol. 19, No. 6 (Nov/Dec 2001), pp. 2268-2279. | |
| | C18 | Currie <i>et al.</i> , "Controlling Threading Dislocation Densities in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," <u>Applied Physics Letters</u> , Vol. 72, Issue 14 (April 6, 1998), pp. 1718-1720. | |
| | C19 | Eaglesham <i>et al.</i> , "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990), pp. 1943-1946. | |
| | C20 | Feijoo <i>et al.</i> , "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pp. 493-496. | |
| | C21 | Fischetti <i>et al.</i> , "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>Journal of Applied Physics</u> , Vol. 80, No. 4 (August 15, 1996), pp. 2234-2252. | |
| | C22 | Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electron mobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001), pp. 1232-1250. | |
| | C23 | Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61. | |
| | C24 | Fitzgerald <i>et al.</i> , "Relaxed GexSi1-x structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>Journal of Vacuum Science Technology</u> , B 10(4) (Jul/August 1992), pp. 1807-1819. | |
| EXAMINER | | DATE CONSIDERED | |

| | | |
|---|---|--|
| FORM PTO – 1449 INFORMATION DISCLOSURE STATEMENT | | ATTORNEY DOCKET NO.: ASC-044C1 APPLICANT(S): Fitzgerald <i>et al.</i> SERIAL NO.: 10/611,739 FILING DATE: July 1, 2003 GROUP: 2818 |
| OTHER ART, JOURNAL ARTICLES, ETC. | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | |
| | C25 | Fitzgerald <i>et al.</i> , "Totally Relaxed GexSi1-x Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pp. 811-813. |
| | C26 | Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277. |
| | C27 | Gray <i>et al.</i> , "Analysis and Design of Analog Integrated Circuits," John Wiley & Sons, 1984, pp. 605-632. |
| | C28 | Grützmacher <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533. |
| | C29 | Hackbarth <i>et al.</i> , "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151. |
| | C30 | Hackbarth <i>et al.</i> , "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999), pp. 734-738. |
| | C31 | Herzog <i>et al.</i> , "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u> , Vol. 380 (2000), pp. 36-41. |
| | C32 | Höck <i>et al.</i> , "Carrier mobilities in modulation doped Si1-xGex heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998), pp. 141-144. |
| | C33 | Höck <i>et al.</i> , "High hole mobility in Si0.17 Ge0.83 channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Vol. 76, No. 26 (June 26, 2000), pp. 3920-3922. |
| | C34 | Höck <i>et al.</i> , "High performance 0.25 µm p-type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998), pp. 1888-1889. |
| | C35 | Huang <i>et al.</i> , "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682. |
| | C36 | Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036. |
| | C37 | Ishikawa <i>et al.</i> , "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," Proceedings of the 1997 IEEE International SOI Conference (October 1997), pp. 16-17. |
| | C38 | Ishikawa <i>et al.</i> , "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985. |
| | C39 | Ismail <i>et al.</i> , "Modulation-doped n-type Si/SiGe with inverted interface," <u>Applied Physics Letters</u> , Vol. 65, No. 10 (September 5, 1994), pp. 1248-1250. |
| | C40 | Ismail, "Si/SiGe High-Speed Field-Effect Transistors," Electron Devices Meeting, Washington, D.C., (December 10, 1995), pp. 20.1.1-20.1.4. |
| | C41 | Kearney <i>et al.</i> , "The effect of alloy scattering on the mobility of holes in a Si1-xGex quantum well," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 174-180. |
| | C42 | Kim <i>et al.</i> , "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," <u>IEEE Microwave and Guided Wave Letters</u> , Vol. 8, No. 8 (August 1998), pp. 293-295. |
| | C43 | Koester <i>et al.</i> , "Extremely High Transconductance Ge/Si0.4Ge0.6 p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000), pp. 110-112. |
| | C44 | König <i>et al.</i> , "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547. |
| EXAMINER | | DATE CONSIDERED |

| | | |
|-----------------------------------|--|---|
| FORM PTO – 1449 | | ATTORNEY DOCKET NO.: ASC-044C1 |
| INFORMATION DISCLOSURE STATEMENT | | APPLICANT(S): Fitzgerald <i>et al.</i> |
| | | SERIAL NO.: 10/611,739 |
| | | FILING DATE: July 1, 2003 GROUP: 2818 |
| OTHER ART, JOURNAL ARTICLES, ETC. | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | |
| | C45 | König <i>et al.</i> , "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993), pp. 205-207. |
| | C46 | König <i>et al.</i> , "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995), pp. 1595-1602. |
| | C47 | Kummer <i>et al.</i> , "Low energy plasma enhanced chemical vapor deposition," <u>Materials Science and Engineering</u> , B89 (2002), pp. 288-295. |
| | C48 | Kuznetsov <i>et al.</i> , "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>Journal of Vacuum Science and Technology</u> , B 13(6) (November/December 1995), pp. 2892-2896. |
| | C49 | Larson, "Integrated Circuit Technology Options for RFIC's Present Status and Future Directions," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3 (March 1998), pp. 387-399. |
| | C50 | Lee <i>et al.</i> , "CMOS RF Integrated Circuits at 5 GHz and Beyond," <u>Proceedings of the IEEE</u> , Vol. 88, No. 10 (October 2000), pp. 1560-1571. |
| | C51 | Lee <i>et al.</i> , "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si1-xGex/Si virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 20 (November 12, 2001), pp. 3344-3346. |
| | C52 | Lee <i>et al.</i> , "Strained Ge channel p-type MOSFETs fabricated on Si1-xGex/Si virtual substrates," <u>Materials Research Society Symposium Proceedings</u> , Vol. 686 (2002), pp. A1.9.1-A1.9.5. |
| | C53 | Leitz <i>et al.</i> , "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," <u>Materials Research Society Symposium Proceedings</u> , Vol. 686 (2002), pp. A3.10.1-A3.10.6. |
| | C54 | Leitz <i>et al.</i> , "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001), pp. 2730-2736. |
| | C55 | Leitz <i>et al.</i> , "Hole mobility enhancements in strained Si/Si1-yGey p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si1-xGex (x<y) virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 25 (December 17, 2001), pp. 4246-4248. |
| | C56 | Li <i>et al.</i> , "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>Journal of Vacuum Science and Technology A</u> , Vol. 20, No.3 (May/June 2002), pp. 1030-1033. |
| | C57 | Lu <i>et al.</i> , "High Performance 0.1 μ m Gate-Length P-Type SiGe MODFET's and MOS-MODFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 8 (August 2000), pp. 1645-1652. |
| | C58 | Maiti <i>et al.</i> , "Strained-Si heterostructure field effect transistors," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 1225-1246. |
| | C59 | Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 341-347. |
| | C60 | Meyerson <i>et al.</i> , "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," <u>Applied Physics Letters</u> , Vol. 53, No. 25 (December 19, 1988), pp. 2555-2557. |
| | C61 | Mizuno <i>et al.</i> , "Advanced SOI-MOSFETs with Strained-Si Channel for High Speed CMOS-Electron/Hole Mobility Enhancement," 2002 Symposium on VLSI Technology, Honolulu (June 13-15), <u>IEEE New York</u> , pp. 210-211. |
| | C62 | Mizuno <i>et al.</i> , "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 5 (May 2000), pp. 230-232. |
| EXAMINER | | DATE CONSIDERED |

| | | |
|-----------------------------------|--|--|
| FORM PTO – 1449 | | ATTORNEY DOCKET NO.: ASC-044C1 |
| INFORMATION DISCLOSURE STATEMENT | | APPLICANT(S): Fitzgerald <i>et al.</i> |
| | | SERIAL NO.: 10/611,739 |
| | | FILING DATE: July 1, 2003 GROUP: 2818 |
| OTHER ART, JOURNAL ARTICLES, ETC. | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | |
| | C63 | Mizuno <i>et al.</i> , "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE IDEM Technical Digest</u> (1999 International Electron Device Meeting), pp. 934-936. |
| | C64 | Nayak <i>et al.</i> , "High-Mobility Strained-Si PMOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 10 (October 1996), pp. 1709-1716. |
| | C65 | O'Neill <i>et al.</i> , "SiGe virtual substrate N-channel heterojunction MOSFETS," <u>Semiconductor Science and Technology</u> , Vol. 14 (1999), pp. 784-789. |
| | C66 | "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates," <u>IBM Technical Disclosure Bulletin</u> , Vol. 32, No. 8A (January 1990), pp. 330-331. |
| | C67 | Papananos, "Radio-Frequency Microelectronic Circuits for Telecommunication Applications," Kluwer Academic Publishers, 1999, pp. 115-117, 188-193. |
| | C68 | Parker <i>et al.</i> , "SiGe heterostructure CMOS circuits and applications," <u>Solid State Electronics</u> , Vol. 43 (1999), pp. 1497-1506. |
| | C69 | Ransom <i>et al.</i> , "Gate-Self-Aligned n-channel and p-channel Germanium MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 12 (December 1991), pp. 2695. |
| | C70 | Reinking <i>et al.</i> , "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," <u>Electronics Letters</u> , Vol. 35, No. 6 (March 18, 1999), pp. 503-504. |
| | C71 | Rim <i>et al.</i> , "Enhanced Hole Mobilities in Surface-Channel Strained-Si p-MOSFETs," <u>IEDM</u> (1995), pp. 517-520. |
| | C72 | Rim <i>et al.</i> , "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 7 (July 2000), pp. 1406-1415. |
| | C73 | Rim, "Application of Silicon-Based Heterostructures to Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1999, pp. 1-184. |
| | C74 | Robbins <i>et al.</i> , "A model for heterogeneous growth of Si _{1-x} Ge _x films for hydrides," <u>Journal of Applied Physics</u> , Vol. 69, No. 6 (March 15, 1991), pp. 3729-3732. |
| | C75 | Sadek <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Transactions on Electron Devices</u> (August 1996), pp. 1224-1232. |
| | C76 | Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u> , Vol. 12 (1997), pp. 1515-1549. |
| | C77 | Sugimoto <i>et al.</i> , "A 2V, 500 MHz and 3V, 920 MHz Low-Power Current-Mode 0.6 μ m CMOS VCO Circuit," <u>IEICE Trans Electron</u> , Vol. E82-C, No. 7 (July 1999), pp. 1327-1329. |
| | C78 | Ternent <i>et al.</i> , "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits," <u>IEEE</u> (October 2000), pp. 38-43. |
| | C79 | Tweet <i>et al.</i> , "Factors determining the composition of strained GeSi layers grown with disilane and germane," <u>Applied Physics Letters</u> , Vol. 65, No. 20 (November 14, 1994), pp. 2579-2581. |
| | C80 | Usami <i>et al.</i> , "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semiconductor Science and Technology</u> , (1997), abstract. |
| | C81 | Welser <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," <u>IEEE Electron Device Letters</u> , Vol. 15, No. 3 (March 1994), pp. 100-102. |
| EXAMINER | | DATE CONSIDERED |

| | | |
|-----------------------------------|--|--|
| FORM PTO – 1449 | | ATTORNEY DOCKET NO.: ASC-044C1 |
| INFORMATION DISCLOSURE STATEMENT | | APPLICANT(S): Fitzgerald <i>et al.</i> |
| | | SERIAL NO.: 10/611,739 |
| | | FILING DATE: July 1, 2003 GROUP: 2818 |
| OTHER ART, JOURNAL ARTICLES, ETC. | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | |
| | C82 | Welser <i>et al.</i> , "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," <u>IEEE IDEM Technical Digest</u> (1993 International Electron Devices Meeting), pp. 545-548. |
| | C83 | Welser <i>et al.</i> , "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," <u>IEEE IDEM Technical Digest</u> (1992 International Electron Devices Meeting), pp. 1000-1002. |
| | C84 | Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1994, pp. 1-205. |
| | C85 | Wolf <i>et al.</i> , "Silicon Processing for the VLSI Era, Vol. 1: Process Technology," Lattice Press, Sunset Beach, CA, 1986, pp. 384-386. |
| | C86 | Xie <i>et al.</i> , "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," <u>The Physical Review Letters</u> , Vol. 73, No. 22 (November 28, 1994), pp. 3006-3009. |
| | C87 | Xie <i>et al.</i> , "Very High Mobility Two-Dimensional Hole Gas in Si/GexSi1-x/Ge Structures Grown by Molecular Beam Epitaxy," <u>Applied Physics Letters</u> , Vol. 63, Issue 16 (October 18, 1993), pp. 2263-2264. |
| | C88 | Xie, "SiGe Field Effect Transistors," <u>Materials Science and Engineering</u> , Vol. 25 (1999), pp. 89-121. |
| | C89 | Yeo <i>et al.</i> , "Nanoscale Ultra-Thin-Body Silicon-on-Insulator P-MOSFET with a SiGe/Si Heterostructure Channel," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 4 (April 2000), pp. 161-163. |
| | C90 | Zhang <i>et al.</i> , "Demonstration of a GaAs-Based Compliant Substrate Using Wafer Bonding and Substrate Removal Techniques," Electronic Materials and Processing Research Laboratory, Department of Electrical Engineering, University Park, PA 16802, 1998, pp. 25-28. |
| | C91 | "2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," <u>IBM Technical Disclosure Bulletin</u> , Vol. 35, No. 4B (September 1992), pp. 136-140. |
| EXAMINER | | DATE CONSIDERED |

3052366